**Philips Semiconductors** 

**Product specification** 

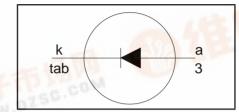
# Rectifier diodes Schottky barrier

## PBYR1045B series

### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

### **SYMBOL**



### QUICK REFERENCE DATA

$$V_R = 40 \text{ V}/45 \text{ V}$$

$$I_{F(AV)} = 10 \text{ A}$$

$$V_F \le 0.57 \text{ V}$$

### **GENERAL DESCRIPTION**

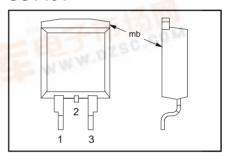
Schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1045B series is supplied in the surface mounting SOT404 package.

### **PINNING**

PIN	DESCRIPTION	
1	no connection	
2	cathode <sup>1</sup>	
3	anode	
tab	cathode	

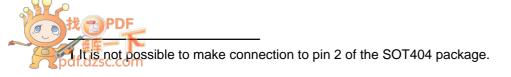
### **SOT404**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V
$I_{FRM}$ Repetitive peak forward current     square wave; δ = 0.5; $T_{mb} \le 136$ °C     -     20 $I_{FSM}$ Non-repetitive peak forward current     t = 10 ms t = 8.3 ms     -     135 t = 8.3 ms	V
current Non-repetitive peak forward current t = 10 ms t = 8.3 ms - 150	А
current   t = 8.3 ms   -   150	А
I surge: with reapplied Vocasion	AAA
$I_{RRM}  \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	A
T <sub>j</sub> Operating junction temperature - 150	°C
T <sub>stg</sub> Storage temperature - 65 175	°C



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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance junction			-	2	K/W
R <sub>th j-a</sub>	to mounting base Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	ı	50	-	K/W

# **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified

	•					
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{F}$	Forward voltage	$I_{\rm F} = 10 \text{ A}; T_{\rm i} = 125 ^{\circ}\text{C}$	-	0.5	0.57	V
1 '		$I_{\rm F} = 20 \text{ A}; T_{\rm i} = 125 ^{\circ}\text{C}$	-	0.69	0.72	V
		$I_{\rm F} = 20  {\rm A}^{\prime}$	-	0.65	0.84	V
I <sub>R</sub>	Reverse current	$ \dot{V}_{R} = V_{RWM} $	-	0.2	1.3	mΑ
''		$V_{R} = V_{RWM}$ ; $T_{i} = 100^{\circ}C$	-	22	35	mΑ
C <sub>d</sub>	Junction capacitance	$V_R^2 = 5 \hat{V}_1^2 \hat{f} = 1 \text{ MHz}, T_1 = 25 \hat{C} \text{ to } 125 \hat{C}$	-	350	-	pF

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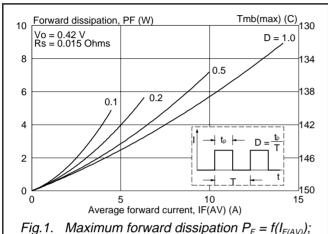


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)});$  square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$ 

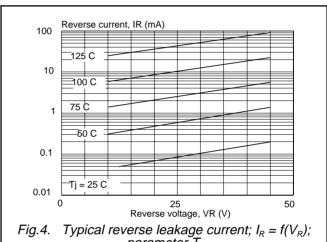


Fig.4. Typical reverse leakage current;  $I_R = f(V_R)$ ; parameter  $T_i$ 

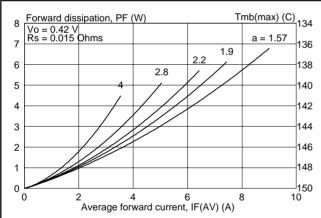
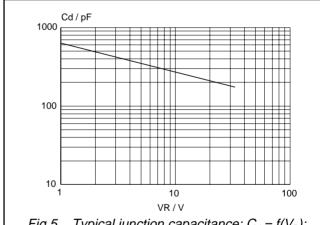


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$ ; sinusoidal current waveform where  $a = f(I_{F(AV)})$ ;  $factor = I_{F(RMS)} / I_{F(AV)}$ .



Typical junction capacitance;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25 ^{\circ}\text{C}$  to  $125 ^{\circ}\text{C}$ . Fig.5.

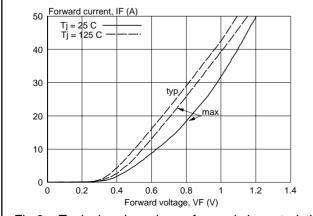


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

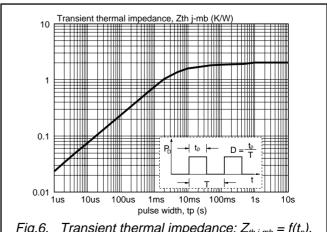
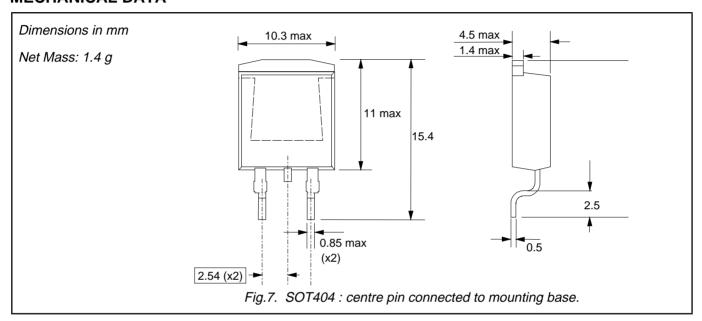


Fig.6. Transient thermal impedance;  $Z_{th j-mb} = f(t_p)$ .

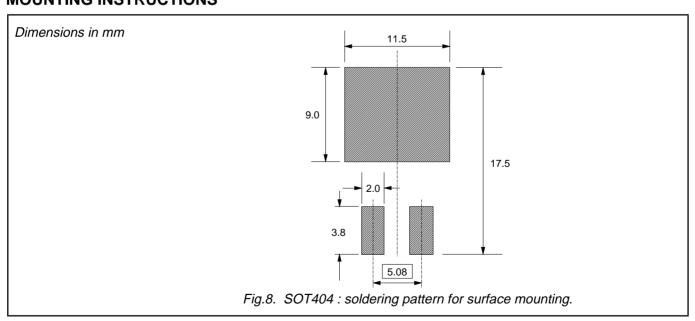
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### **MECHANICAL DATA**



## **MOUNTING INSTRUCTIONS**



### **Notes**

- Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
   Epoxy meets UL94 V0 at 1/8".

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Rectifier	diodes
Schottky	barrier

PBYR1045B series

### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la				
Product specification This data sheet contains final product specifications.				
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#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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